

## 30V P-Channel Power MOSFET



SOP-8



#### Pin Definition:

1. Source 8. Drain
2. Source 7. Drain
3. Source 6. Drain
4. Gate 5. Drain

Key Parameter Performance

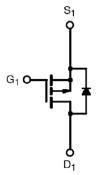
Parameter		Value	Unit	
$V_{ t DS}$		-30	٧	
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> =-10V	60		
	V <sub>GS</sub> =-4.5V	90	mΩ	
$Q_g$		5.1	nC	

## **Ordering Information**

Part No.	Package	Packing		
TSM600P03CS RLG	SOP-8	2.5kps / 13" Reel		

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

### **Block Diagram**



P-Channel MOSFET

#### **Absolute Maximum Ratings** (Tc = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current*	Tc = 25ºC	I <sub>D</sub>	-4.7	Α
	Tc = 100°C		-3	Α
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	-18.8	Α
Power Dissipation @ T <sub>C</sub> = 25°C		$P_{D}$	2.1	W
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	50	°C/W	



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**Electrical Specifications** (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	-30			V
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -3A$	R <sub>DS(ON)</sub>		44	60	mΩ
	$V_{GS} = -4.5V, I_D = -2A$			73	90	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(TH)}$	-1.2	-1.6	-2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = -30V, T_{J} = 25^{\circ}C$				-1	μА
	$V_{DS} = -24V, T_{J} = 125^{\circ}C$	$I_{DSS}$			-10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Forward Transconductance (Note 2)	$V_{DS} = -10V, I_{D} = -3A$	g <sub>fs</sub>		3.5		S
Dynamic						
Total Gate Charge (Note 2,3)	$V_{DS} = -15V, I_{D} = -3A,$ $V_{GS} = -4.5V$	$Q_g$		5.1		nC
Gate-Source Charge (Note 2,3)		$Q_{gs}$		2		
Gate-Drain Charge (Note 2,3)		$Q_{gd}$		2.2		
Input Capacitance	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	C <sub>iss</sub>		560		pF
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$	$C_{oss}$		55		
Reverse Transfer Capacitance	f = 1.0MHz	$C_{rss}$		40		
Switching						
Turn-On Delay Time (Note 2,3)		t <sub>d(on)</sub>		3.4		
Turn-On Rise Time (Note 2,3)	$V_{DD} = -15V, I_{D} = -1A,$	t <sub>r</sub>		10.8		
Turn-Off Delay Time (Note 2,3)	$V_{GS} = -10V$ , $R_G = 6\Omega$	$t_{d(off)}$		26.9		ns
Turn-Off Fall Time (Note 2,3)		t <sub>f</sub>		6.9		
Source-Drain Diode Ratings and Ch	aracteristic					
Maximum Continuous Drain-Source	Integral reverse diode in	_			4.7	
Diode Forward Current		I <sub>S</sub>			-4.7	Α
Maximum Pulse Drain-Source Diode	the MOSFET	I <sub>SM</sub>			-18.8	Α
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = -1A$	$V_{\sf SD}$			-1	V

#### Note:

- 1. Pulse width limited by safe operating area
- 2. Pulse test: pulse width ≤300µs, duty cycle ≤2%
- 3. Switching time is essentially independent of operating temperature.

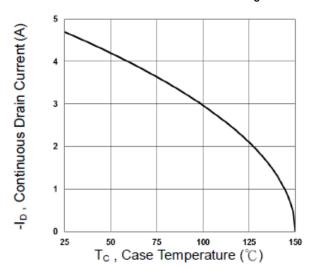


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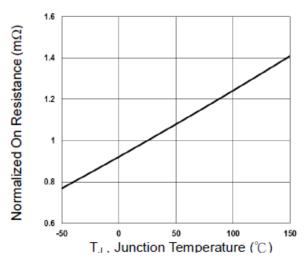


#### **Electrical Characteristics Curve**

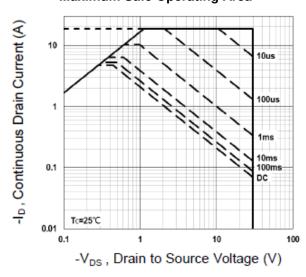
#### Continuous Drain Current vs. Tc



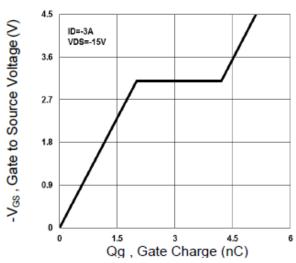
#### On-Resistance vs. Junction Temperature



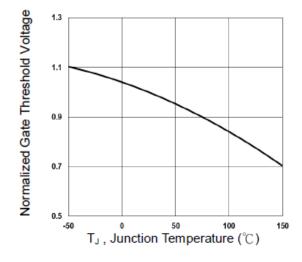
#### **Maximum Safe Operating Area**



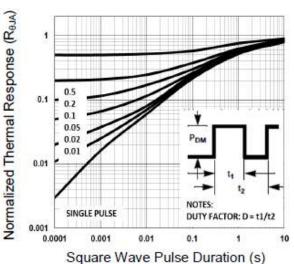
**Gate Charge** 



#### Threshold Voltage vs. Junction Temperature



#### **Normalized Thermal Transient Impedance Curve**

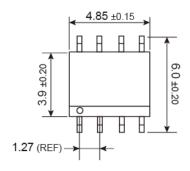


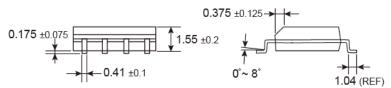


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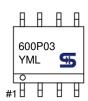
## **SOP-8 Mechanical Drawing**





Unit: Millimeters

#### **MARKING DIAGRAM**



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

Version: B1612



## SEMICONDUCTOR

# TSM600P03CS 30V P-Channel Power MOSFET



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